PAPER-II ELECTRONIC SCIENCE

Si	gnature and Name of Invigilator		
1.	(Signature)	C	OMR Sheet No. :
	(Name)		(To be filled by the Candidate)
2.	(Signature)	R	Roll No.
	(Name)		(In figures as per admission card)
		R	Coll No
•	J ð ð 1 6		(In words)
Ti	me : $1^{1/4}$ hours]		[Maximum Marks : 100
Νι	umber of Pages in this Booklet : 16		Number of Questions in this Booklet : 50
	Instructions for the Candidates		परीक्षार्थियों के लिए निर्देश
1.	Write your roll number in the space provided on the top of this page.	1. 2.	इस पृष्ठ के ऊपर नियत स्थान पर अपना रोल नम्बर लिखिए । इस प्रश्न-पत्र में पचास बहुविकल्पीय प्रश्न हैं ।
2.	This paper consists of fifty multiple-choice type of questions.	3.	पराक्षा प्रारम्भ होने पर, प्रश्न-पुस्तिका आपको द दो जीयगी । पहले पाँच मिनट आपको प्रश्न-प्रस्तिका खोलने तथा उसकी निम्नलिखित
5.	will be given to you. In the first 5 minutes, you are requested		जाँच के लिए दिये जायेंगे, जिसकी जाँच आपको अवश्य करनी है :
	to open the booklet and compulsorily examine it as below :		(i) प्रश्न-पुस्तिका खोलने के लिए पुस्तिका पर लगी कागज की सील
	(1) To have access to the Question Booklet, tear off the paper seal on the edge of this cover page. Do not accept		को फोड़ ले । खुला हुई यो बिना स्टोकर-साल को पुस्तिको स्वीकार न करें ।
	a booklet without sticker-seal and do not accept an open		(ii) कवर पृष्ठ पर छपे निर्देशानुसार प्रश्न-पुस्तिका के पृष्ठ तथा
	booklet.		प्रश्नों की संख्या को अच्छी तरह चैक कर लें कि ये पूरे
	(1) Tally the number of pages and number of questions in the booklet with the information printed on the		हे । दोषपूर्ण पुस्तिका जिनमें पृष्ठ/प्रश्न कम हो या दुबारा आ गरो टों या मीनियल में न टों अर्थान किमी भी एकप की
	cover page. Faulty booklets due to pages/questions		त्रिपर्ण पस्तिका स्वीकार न करें तथा उसी समय उसे
	missing or duplicate or not in serial order or any		लौटाकूर उसके स्थान पर दूसरी सही प्रश्न-पुस्तिका ले लें ।
	by a correct booklet from the invigilator within the		इसके लिए आपको पाँच मिनट दिये जायेंगे । उसके बाद न जो आपको प्राप्त नामन जो जायेंगी और न नी आपको
	period of 5 minutes. Afterwards, neither the Question		ता आपको प्रश्न-पुरस्तको योपस लो जावना आर न हो आपको अतिरिक्त समय दिया जावेगा ।
	Booklet will be replaced nor any extra time will be		(iii) इस जाँच के बाद प्रश्न-पुस्तिका का नंबर OMR पत्रक पर अंकित करें
	(iii) After this verification is over, the Test Booklet Number		और OMR पत्रक का नंबर इस प्रश्न-पुस्तिका पर अंकित कर दे ।
	should be entered on the OMR Sheet and the OMR	4.	प्रत्यक प्रश्न के लिए चार उत्तर विकल्प (1), (2), (3) तथा (4) दिये गय हैं । आपको सही उत्तर के वत्त को पेन से भरकर काला करना है जैस
4	Sheet Number should be entered on this Test Booklet.		कि नीचे दिखाया गया है :
4.	and (4). You have to darken the circle as indicated below on		उदाहरण : 🕕 🕘 🌑 🕘
	the correct response against each item.	-	जबकि (3) सही उत्तर है ।
	Example: (1) (2) \bullet (4)	5.	प्रश्नी के उत्तर कवल प्रश्न पुस्तिकों के अन्दर दिये गय OMK पत्रके पर ही अंकित करने हैं । यदि आप OMP पत्रक पर दिये गये वन के अलाव
5	Your responses to the items are to be indicated in the OMR		किसी अन्य स्थान पर उत्तर चिह्नांकित करते हैं, तो उसका मुल्यांकन
5.	Sheet given inside the Booklet only. If you mark your		नहीं होगा ।
	response at any place other than in the circle in the OMR	6.	अन्दर दिये गये निर्देशों को ध्यानपूर्वक पढ़ें ।
6	Sheet, it will not be evaluated.	7.	केच्ची कीम (Rough Work) इस पुस्तिकों के आन्तम पृष्ठ पर कर । यदि आप OMP पुत्रक पर नियत अपन के अलावा आजा जोल
0. 7.	Rough Work is to be done in the end of this booklet.	0.	नम्बर फोन नम्बर या कोई भी ऐसा चिहन जिससे आपकी पहचान हो
8.	If you write your Name, Roll Number, Phone Number or put		सके, अंकित करते हैं अथवा अभद्र भाषा का प्रयोग करते हैं, या कोई
	any mark on any part of the OMR Sheet, except for the space		अन्य अनुचित साधन का प्रयोग करते हैं, जैसे कि अंकित किये गये
	allotted for the relevant entries, which may disclose your identity or use abusive language or employ any other unfair.		उत्तर को मिटाना या सफेद स्याही से बदलना तो परीक्षा के लिये
	means, such as change of response by scratching or using	0	अयोग्य धार्षित किये जा सकत है । आगलो गणिश्च सामान होने पर पल OMP पत्रक निर्माश्वक प्रहोटरा के
	white fluid, you will render yourself liable to disqualification.	9.	लौटाना आवश्यक है और परीक्षा समापित के बाद उसे अपने साथ परीक्षा भवन
9.	You have to return the Original OMR Sheet to the invigilators		से बाहर न लेकर जायें । हालांकि आप परीक्षा समाप्ति पर मूल प्रश्न-पुस्तिका
	at the end of the examination compulsorily and must not carry it with you outside the Examination Hall. You are		तथा OMR पत्रक की डुप्लीकेट प्रति अपने साथ ले जा सकते हैं ।
	however, allowed to carry original question booklet and	10.	कवल C.B.S.E. द्वारा प्रदान किये गये काले बाल प्वाइंट पेन का जी नानेपाल नहें ।
	duplicate copy of OMR Sheet on conclusion of examination.	11	हा इस्तमाल कर । किसी भी प्रकार का संगणक (कैलकलेटर) या लाग टेबल आदि का
10.	Use only Black Ball point pen provided by C.B.S.E.		प्रयोग वर्जित है ।
12.	There is no negative marks for incorrect answers.	12.	गलत उत्तरों के लिए कोई नकारात्मक अंक नहीं हैं ।
	J-88-16	1	Р.Т.О.

ELECTRONIC SCIENCE Paper – II

- Note: This paper contains fifty (50) objective type questions of two (2) marks each. All questions are compulsory.
- 1. In a circuit shown below the base current is



(1)	2.55 μΑ	(2)	5.4 µA
(3)	2.66 μΑ	(4)	3.6 µA

The threshold voltage of CMOS inverter ($V_{th} = V_{in} = V_{out}$) can be expressed as 2.



3. Consider a unity feedback control system as shown in the following figure : E(S)C(S)G(S)

The steady state error is given as

Paper-II		2	
(3)	$\lim_{s \to 0} \frac{GR(S)}{1 - G(S)}$	(4)	$\lim_{s \to 0} \frac{R(S)}{1 - SG(S)}$
	r = SR(S)		$\mathbf{R}(\mathbf{S})$
(1)	$\lim_{s \to 0} \frac{\mathbf{R}(S)}{1 + \mathbf{SG}(S)}$	(2)	$\lim_{s \to 0} \frac{GR(S)}{1 + G(S)}$
	$\mathbf{R}(\mathbf{S})$		r = SR(S)



4. A conducting line on an IC chip is 2.8 mm long and has a rectangular cross-section 1×4 micrometer. A current of 5 mA produces a voltage drop of 100 mV across the line. If the electron mobility is 500 cm²/V.s., the electron concentration is

(1)	$4.38 \times 10^{21} \text{ cm}^{-3}$	(2)	$4.38 \times 10^{27} \text{ cm}^{-3}$
(3)	$3.98 \times 10^{21} \text{ cm}^{-3}$	(4)	$4.29 \times 10^{27} \text{ cm}^{-3}$

5. In emitter bias configuration, the stability factor $S(I_{CO})$ is defined as



6. The following state diagram belongs to



7. 8086 is interfaced to two 8259s (programmable interval timer). If 8259s are in master slave configuration, the number of interrupts available to the 8086 microprocessor is

(1)	8	(2)	16
(3)	32	(4)	64

- **8.** A function q that accepts a pointer to a character as argument and returns a pointer to an array of integer, can be declared as
 - (1) int * q (char *) [] (2) int (* q (char *)) []
 - (3) int (* q) (char *) [] (4) None of the above
- **9.** TRAPATT is used as
 - (1) amplifier in radars
 - (2) local oscillator in radars
 - (3) switch in communication systems
 - (4) low frequency oscillator

J-88-16

10. Tunnel diode is used as

- (1)High speed switch (2)Clipper
- (3)Low gain amplifier (4)Low frequency oscillator
- The fourier series of the following figure is 11.



- 12. Which of the following cannot be the Fourier series expansion of a periodic signal ?
 - $x(t) = 2\cos \pi t + 7\cos t$ $x(t) = 2\cos t + 3\cos 3t$ (2)(1)
 - $x(t) = \cos t + 0.5$ $x(t) = 2 \cos 1.5 \pi t + \sin 3.5 \pi t$ (4)(3)

13. The main advantage of TDM over FDM is that it

- needs less bandwidth (1)needs less power (2)(3) needs simple circuitry (4)
- gives better signal / noise ratio
- TDM stands for Time Division Multiplexing

FDM stands for Frequency Division Multiplexing

14. Consider the RC circuit shown in the following figure



The differential equation of the system will be

(2) $\frac{\mathrm{d}\mathbf{e}_{i}(t)}{\mathrm{d}t} = \frac{1}{\mathrm{RC}} \frac{\mathrm{d}\mathbf{e}_{o}(t)}{\mathrm{d}t} + \mathbf{e}_{o}(t)$ (1) $\frac{\mathrm{d}\mathbf{e}_{i}(t)}{\mathrm{d}t} = \frac{\mathbf{e}_{o}(t)}{\mathrm{RC}} + \frac{\mathrm{d}\mathbf{e}_{o}(t)}{\mathrm{d}t}$ $\frac{1}{RC}\frac{de_{i}(t)}{dt} = \frac{1}{RC}\frac{de_{o}(t)}{dt} - e_{o}(t)$ (4) $\frac{\mathrm{d}\mathbf{e}_{i}(t)}{\mathrm{d}t} = \frac{\mathbf{e}_{o}(t)}{\mathrm{RC}} - \frac{\mathrm{d}\mathbf{e}_{o}(t)}{\mathrm{d}t}$ (3)

15. The state-space model of a system is given as

$$\begin{bmatrix} \dot{x}_1 \\ \dot{x}_2 \end{bmatrix} = \begin{bmatrix} 1 & 0 \\ 1 & 1 \end{bmatrix} \begin{bmatrix} x_1 \\ x_2 \end{bmatrix} + \begin{bmatrix} 1 \\ 1 \end{bmatrix} u(t)$$

where u(t) is a unit step input occurring at t = 0 and $x(0) = \begin{bmatrix} 1 \\ 0 \end{bmatrix}$.
The time response of the system is

(1)
$$\begin{bmatrix} 2e^{t} + 1 \\ 2t e^{-t} \end{bmatrix}$$

(2) $\begin{bmatrix} 2e^{t} - 1 \\ 2t e^{t} \end{bmatrix}$
(3) $\begin{bmatrix} 2e^{-t} + 1 \\ 2t e^{-t} \end{bmatrix}$
(4) $\begin{bmatrix} e^{-t} + 1 \\ 2 e^{t} \end{bmatrix}$

16. If 'L' is the length, 'W' is the width and 't' is the thickness of a semiconductor layer to form a resistor, the sheet resistance is defined as

(a)
$$\frac{\rho}{t}$$
 (b) $\frac{\rho L}{tA}$
(c) $\frac{R}{t}$ (d) $\frac{RW}{L}$

Out of the above which one is correct?

- (1) (a) and (b) are correct. (2) (b) and (d) are correct.
- (3) (a) and (d) are correct. (4) (b) and (c) are correct.

17. The typical dB magnitude versus characteristics of the compensators is given below :



- (a) (i) is log compensator and (ii) is lead compensator
- (b) (ii) is lead compensator and (i) is log compensator
- (c) (ii) is lead compensator and (iii) is log compensator
- (d) (i) is log compensator and (ii) is log-lead compensator Which of the above are correct ?
- (1) (a) and (b) (2) (b) and (c)
- (3) (a) and (d) (4) (b) and (d)

18. In reverse bias abrupt p-n junction the depletion region thickness is

(a)
$$\sqrt{\frac{2\epsilon_{si}}{q} \left(\frac{N_A + N_D}{N_A N_D}\right)} (\phi_o - V)$$
 (b) $\sqrt{\frac{2\epsilon_{si}}{q} \left(\frac{N_A N_D}{N_A + N_D}\right)} (\phi_o - V)$
(c) $\sqrt{\frac{2\epsilon_{si}}{q} \left(\frac{N_A - N_D}{N_A + N_D}\right)} (V - \phi_o)$ (d) $\sqrt{\frac{2\epsilon_{si}}{q} \left(\frac{N_A N_D}{N_A - N_D}\right)} V$

Out of these which is correct answer

(1) (a) is correct and (b) is wrong

21.

Paper-II

(3) (a) and (b) are correct

```
'D/
(' 'A
```

(2) (b) is correct and (c) is wrong

- (4) (d) is correct and (a) is wrong
- 19. For the counter to count upwards starting from 0000 to 1111, following statement are given :

(a)	LOAD input is high	(b)	LOAD input is high
(c)	CLEAR is high	(d)	Enable input is low

(c) CLEAR is high (d) Out of the above, the following is the correct answer :

(1)(a), (b) and (d) (2)(b), (c) and (d)

- (3) (a), (c) and (d) (b) and (c) (4)
- Assume that the 8255 gets selected whenever A15 A11 are high during I/O read or write 20. cycles. The A2 and A1 are connected to A1 and A0 of 8255 chip, then the address for port C of 8255 is

6

(a)	FEh	(b)	03h
(c)	FF03h	(d)	FFh
Cod	es :		
(1)	(a) and (b) are correct	(2)	(c) and (d) are correct
(3)	(a) and (d) are correct	(4)	(b) and (d) are correct
A fu	nction xyz is defined as :		
Voic	d xyz (int $a = 0$, int b, int $c = 0$)		
{			
	cout << a << b << c;		
}			
Whi	ch of the following calls are illegal	?	
(Ass	sume h, g are declared as integers)		
(a)	xyz();	(b)	xyz (h, h) ;
(c)	xyz (h);	(d)	xyz (g, g);
Cod	es :		
(1)	(a) and (c) are correct	(2)	(b) and (d) are correct
(3)	(a) and (b) are correct	(4)	(b) and (c) are correct

J-88-16

- 22. For transmission lines, following statements are given :
 - (a) For open circuited transmission line VSWR is ∞ .
 - (b) For short circuited transmission line VSWR is 0.
 - (c) For short circuited transmission line VSWR is ∞ .
 - (d) The cut off frequency for TEM wave is 0 Hz.

Out of the above statements, following is correct :

- (1) (a), (b)
- (2) (a), (c)
- (3) (a), (b) and (d)
- (4) (a), (c) and (d)
- **23.** Which of the following statements are correct ?
 - (a) PAM can be detected by a bandpass filter.
 - (b) Flat-top sampling leads to an aperture effect.
 - (c) Noise can be reduced by increasing sampling rate.
 - (d) Pulse code modulation is form of digital modulation.

Codes :

- (1) (a), (b) and (d) are correct
- (2) (a), (b) and (c) are correct
- (3) (a) and (b) are correct
- (4) (b) and (d) are correct
- **24.** A SCR may be turned OFF by
 - (a) Interrupting its anode current.
 - (b) Reversing polarity of its anode cathode voltage.
 - (c) Low current drop out
 - (d) When the gate return to 0 V after the trigger pulse is removed.

Codes :

- (1) (a), (b) and (c) are correct
- (2) (a), (b) and (d) are correct
- (3) (b), (c) and (d) are correct
- (4) (a) and (b) are correct

25. Consider the following statements regarding Fourier transform :

- (a) The Fourier transform of an impulse function is a constant function.
- (b) The Fourier transform of an impulse function is a sine function
- (c) The Fourier transform of a constant function is an impulse function.
- (d) The Fourier transform of a constant function is a signum function.

Which of the above statements are correct?

- (1) (a) and (b) (2) (b) and (c)
- (3) (b) and (d) (4) (a) and (c)

26.	Match	the	follov	wing	lists	:
-----	-------	-----	--------	------	-------	---

	List – I		List – II
a.	MOSFET	i.	$I_{dss} \left(1 - \frac{V_{gs}}{V_p}\right)^2$
b.	JFET	ii.	$K \frac{W}{L} (V_{gs} - V_{th}) V_{ds}$
c.	PN Junction diode	iii.	$I_o\left(e\frac{qV}{kT}-1\right)$
d.	BJT	iv.	$\beta = \frac{I_C}{I_B}$

Codes :

	а	b	С	d
(1)	ii	i	iii	iv
(2)	i	iii	ii	iv
(3)	iii	ii	iv	i
(4)	i	ii	iv	iii

27. Match the following lists :

List – I

- a. Electro-encephalogram
- b. Electro-myogram ii. Eye mo
- c. Electrogastogramd. Electro-oculogram
- Codes :

	а	b	с	d
(1)	ii	iii	iv	i
(2)	iii	iv	i	ii
(3)	iv	i	ii	iii
(4)	i	iii	iv	ii

28. Match the following lists :

		List –	I			List – II
a.	Si-ba	and ga	р		i.	3.3 eV
b.	Ge-b	and g	ap		ii	1.12 eV
c.	Ga A	s ban	d gap		iii.	0.7 eV
d.	Si C band gap				iv.	1.43 eV
Coc	les :					
	a	b	с	d		
(1)	ii	iii	iv	i		
(2)	i	ii	iv	iii		
(3)	ii	i	iii	iv		
(4)	iv	ii	iii	i		

Li	ist	_	II
1	0.0	ti	vit

i.	Electrical activity of brain
ii.	Eye movements

- iii. Electrical activity of skeletal muscles
- iv. Muscle activity in the gastro intestinal

29.	Match	the	follo	wing	lists	:
-----	-------	-----	-------	------	-------	---

	List	– I		List – II
a.	IC 74	4198	i.	Quad D flip flop
b.	IC 7	4175	ii	J K master slave flip flop
c.	IC 74	4104	iii.	8 bit shift register
d.	IC 7	4132	iv.	Quad Schmitt trigger
Co	des :			
	a	b	c	d
(1)	i	ii	iii	iv
(2)	ii	i	iii	iv
(3)	iv	ii	i	iii
(4)	iii	i	ii	iv

i.

30. Match the following in context of 8086 :

List – I

- a. MOV AL, [5923 h]
- b. MOV AL, [BX]c. MOV DL, OAh [BX]
- d. MOV AL, F5h [BP] [SI]

- List II
- Register relative addressing
- ii. Memory operand addressing mode
- iii. Relative base index addressing
- iv. Register indirect addressing

Codes :

	a	b	с	d
(1)	ii	i	iv	iii
(2)	i	ii	iv	iii
(3)	iii	i	ii	iv
(4)	ii	iv	i	iii

31. Match the following lists :

List – I List – II Array Heterogeneous i. a. Union b. ii. Homogeneous Volatile iii. Structure c. Bit-field iv. Qualifier d. **Codes :** b d a С ii iii i (1)iv (2)ii i iv iii i (3) ii iii iv i (4) ii iii iv

32.	Match the following lists :
	.

List – I

- a. VSWR
- b. Reflection coefficient
- c. Propagation coefficient

d. Characteristic impedance

Codes :

	a	b	с	d
(1)	i	iv	ii	iii
(2)	iv	i	iii	ii
(3)	iii	i	ii	iv
(4)	i	iii	iv	ii

33. Match the following lists :

		List –	Ι			List – II	
(Frequency Range)					(Typical Application)		
a.	3001	kHz –	3 MH	[z	i.	FM Broadcasting, TV	
b.	430	ГHz –	750 7	ſHz	ii.	Satellite communication	
c.	30 G	Hz – 3	300 G	Hz	iii.	AM Broadcasting	
d.	30 M	IHz – I	300 N	1Hz	iv.	Optical communication	
Cod	les :						
	а	b	с	d			
(1)	iii	iv	i	ii			
(2)	iii	iv	ii	i			
(3)	iv	iii	i	ii			

34. Match the following lists :

iii

ii

i

(4) iv

	List	t – I			List – II
a.	Phot	odiode	•	i.	Prevent high voltages from
					affecting the system receiving
					the signal.
b.	LAS	ER		ii.	Power consumption is negative
c.	Sola	r cell		iii.	Exhibits increase in reverse
					current with light intensity
d.	Opto	o-coup	ler	iv.	Degenerate semi-conductors
Coo	les :				
	a	b	с	Ċ	l
(1)	iv	iii	i	i	i
(2)	i	iv	ii	ii	i
(3)	i	iv	iii	i	i
(4)	iii	iv	ii	i	





(1)	ii	i	iv	iii
(2)	i	iv	iii	ii
(3)	ii	i	iii	iv
(4)	i	iii	iv	ii

Directions : Question No. 36 to 45 :

The following items consist of two statements, one labelled as "Assertion (A)" and the other labelled as the "Reason (R)". You are to examine the two statements carefully and decide if the Assertion (A) and the Reason (R) are individually true and if so whether the reason is a correct explanation of the assertion. Select your answer to these items using the codes given below and mark your answer accordingly.

Codes :

- (1) Both (A) and (R) are true and (R) is the correct explanation of (A).
- (2) Both (A) and (R) are true, but (R) is not the correct explanation of (A).
- (3) (A) is true, but (R) is false.
- (4) (A) is false, but (R) is true.

36.	Assertion (A)	:	MOSFET can be used to drive high current and high voltage networks
			without drawing current or power from the driving circuits.

Reason (R) : The high input impedances of FET essentially isolates the two parts of the network without the need of optical or electromagnetic linkages.

J-88-16

- **37.** Assertion (A) : Duality is a property of circuit equations.
 - Reason (R) : Two circuits are said to be dual when the mesh equations that describe the behaviour of one circuit are found to be identical in the form of nodal equations that describe the other.
- 38. Assertion (A) : Clippers are networks that employ diodes to clip away a portion of an input signal without distorting the remaining part of the applied waveforms.
 - Reason (R) : In clipper circuit, the orientation of diode is very important and it decide the portion of the wave to be clipped. Clippers may be series or parallel type, depending upon the series/parallel connection of diode with the load.
- **39.** Assertion (A) : In a conservative field the work done in moving from one point to another is independent of the path.
 - Reason (R) : In a conservative field, there is a mechanism for dissipating energy corresponding to positive work done and a source from which energy could be absorbed, if the work were negative.
- 40. Assertion (A) : For DAA instruction in 8086 μP, if four LSBs of register AL are greater than 9 or AC = 1 then 6 is added to the four LSBs of register AL.
 - Reason (R) : Because AL contains binary sum which needs to be converted into BCD sum.

41. Assertion (A) : In 'C' language, if 'a' is name of an array and '++' operator is used to increment the value of 'a' then compiler will flag an error.

Reason (**R**) : 'a' is 'const' type pointer.

- 42. Assertion (A) : Noise margin may be defined as the allowable level of additive noise for proper implementation of logic value at 0 and 1 without any possibility of misinterpretation.
 - **Reason (R)** : Noise Margin (NM), It may be defined as for high level :

 $NM_{H} = V_{1H, min} - V_{OH, min}$

Further for low level, it is defined as :

 $NM_L = V_{IL, max} - V_{OL, max}$

- 43. Assertion (A) : Baseband designates the band of frequencies representing the signal supplied by the source of information.
 - **Reason (R)** : The frequency of baseband signal is equal to the carrier wave signal frequency.
- **44.** Assertion (A) : In Lasers, the photons emitted has the same energy as the incident photon and are in phase with it.
 - **Reason (R)** : The amplitudes of individual photons add to produce a brighter light.
- **45.** Assertion (A) : If the characteristic equation contains any root on the imaginary axis, then the output response will have sustained oscillations.
 - Reason (R) : The poles or the roots of the characteristic equation should not lie in the right half of s-plane for system stability.

J-88-16

Read the passage and answer the following questions numbering from 46 - 50:

The physics of semiconductor devices is dependent on the physics of semiconductors itself. The most important semiconductors are Germanium, Silicon and Gallium Arsenide. The GaAs has different properties than Silicon or Germanium. Pure silicon is intrinsic and contains negligibly small amount of impurities. Each silicon atom shares its four valance electrons with the four neighbouring atoms forming covalent bonds. An extrinsic silicon is achieved by introducing the impurities. The band structure of a solid can be obtained by solving a Schrodinger equation of an approximate one electron problem.

46. The law of mass action in semiconductor is

(1)
$$n + p = n_i^2$$
 (2) $n \cdot p = n_i^2$

(3)
$$\mathbf{n} \cdot \mathbf{p} = \mathbf{n}_{i}$$
 (4) $\mathbf{n}^{2} \mathbf{p} = \mathbf{n}_{i}^{2}$

47. The Fermi-Dirac distribution function is

(1)
$$\frac{1}{1 - \exp\left(\frac{E - E_F}{kT}\right)}$$

(2)
$$\frac{1}{1 + \exp\left(\frac{E - E_F}{kT}\right)}$$

(3)
$$\frac{\Delta E}{1 + \exp\left(\frac{E - E_F}{kT}\right)}$$

(4)
$$\frac{\Delta E}{L + \exp\left(\frac{E - E_F}{kT}\right)}$$

$$1 - \exp\left(\frac{E - E_F}{kT}\right)$$

- **48.** The Fermi level for the extrinsic semiconductor (n-type) lies
 - (1) close to the middle of the bandgap
 - (2) below the conduction band
 - (3) above the conduction band
 - (4) above the valance band

49. The number of ionised donors are given by

$$(1) N_{D}^{+} = N_{D} \left[1 - \frac{1}{1 + \frac{1}{g} \exp\left(\frac{E_{D} - E_{F}}{kT}\right)} \right]$$

$$(2) N_{D}^{+} = N_{D} \left[1 + \frac{1}{1 + \frac{1}{g} \exp\left(\frac{E_{D} - E_{F}}{kT}\right)} \right]$$

$$(3) N_{D}^{+} = N_{D} \left[1 + \frac{1}{g} \exp\left(\frac{E_{D} - E_{F}}{kT}\right) \right]$$

$$(4) N_{D} = N_{D}^{+} \left[1 + \frac{1}{g} \exp\left(\frac{E_{F} - E_{D}}{kT}\right) \right]$$

50. In intrinsic semi-conductor the number of occupied conduction band levels are

(1)
$$\int_{0}^{E_{c}} N(E) F(E) dE$$

(2)
$$\int_{E_{c}}^{E_{top}} N(E) F(E) dE$$

(3)
$$\int_{E_{v}}^{E_{c}} N(E) F(E) dE$$

(4)
$$\int_{E_{c}}^{E_{v}} N(E) F(E) dE$$

J-88-16

Space For Rough Work